

製品概要

FGH50T65SQD-F155: IGBT, 650 V, 50A Field Stop 4 Trench

技術情報は、データシートをご参照ください。

Using novel field stop IGBT technology, ON Semiconductor's new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.

特長

- Maximum Junction Temperature: $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.6\text{ V(Typ.) @ } I_C = 75\text{ A}$
- 100% of the Parts Tested for ILM(1)
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

アプリケーション

- Industrial inverter
- UPS
- Welder
- PFC

電気的仕様

製品	Pricing (\$/Unit)	Compliance	Status	$V_{CES}^{(BR)}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
FGH50T65SQD-F155	2.3066	Pb-free Halide free	Active	650			2.2	0.11	0.402		-	99	-	-	268		TO-247-3

詳細は、弊社 www.onsemi.jp の営業または販売代理店にお問い合わせください。

8/9/2020 作成